

30V N-Channel MOSFET



SOT-23

Pin Definition:



- 1. Gate
- 2. Source
- 3. Drain

PRODUCT SUMMARY

V _{DS} (V)	$R_{DS(on)}(m\Omega)$	I _D (A)
	28 @ V _{GS} = 10V	5.8
30	33 @ V _{GS} = 4.5V	5.0
	52 @ V _{GS} = 2.5V	4.0

Features

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

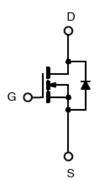
Application

- Load Switch
- PA Switch

Ordering Information

Part No.	Package	Packing
TSM3400CX RF	SOT-23	3Kpcs / 7" Reel

Block Diagram



N-Channel MOSFET

Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	±12	V
Continuous Drain Current	I _D	5.8	А
Pulsed Drain Current	I _{DM}	30	Α
Continuous Source Current (Diode Conduction) ^{a,b}	I _S	2.5	Α
Maximum Power Dissipation @ Ta = 25°C	P _D	1.4	W
Operating Junction Temperature	TJ	+150	°C
Operating Junction and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Thermal Performance

Parameter	Symbol	Limit	Unit	
Junction to Foot Thermal Resistance	R⊖ _{JF}	70	°C/W	
Junction to Ambient Thermal Resistance (PCB mounted)	RΘ _{JA}	90	°C/W	

Notes:

- a. Pulse width limited by the Maximum junction temperature
- b. Surface Mounted on FR4 Board, $t \le 10$ sec.

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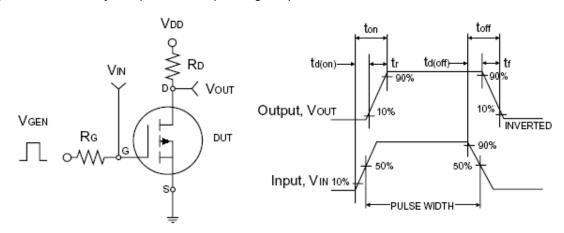


Electrical Specifications (Ta = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV _{DSS}	30			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	$V_{GS(TH)}$	0.7		1.4	V
Gate Body Leakage	$V_{GS} = \pm 12V, V_{DS} = 0V$	I _{GSS}			±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = 24V, V_{GS} = 0V$	I _{DSS}			1.0	μΑ
On-State Drain Current	$V_{DS} = 5V, V_{GS} = 4.5V$	I _{D(ON)}	20			Α
	$V_{GS} = 10V, I_D = 5.8A$			23	28	
Drain-Source On-State Resistance	$V_{GS} = 4.5V, I_D = 5A$	R _{DS(ON)}		28	33	mΩ
	$V_{GS} = 2.5V, I_D = 4A$			43	52	
Forward Transconductance	$V_{DS} = 5V, I_{D} = 5A$	g _{fs}	10	15		S
Diode Forward Voltage	$I_S = 1.0A, V_{GS} = 0V$	V_{SD}		0.76	1.0	V
Dynamic ^b	_			_		
Total Gate Charge	$V_{DS} = 15V, I_D = 5.8A,$ $V_{GS} = 10V$	Q_g		9.7	12	
Gate-Source Charge		Q_gs		1.63		nC
Gate-Drain Charge	V _{GS} = 10V	Q_gd		3.1		
Input Capacitance	V _{DS} = 15V, V _{GS} = 0V, f = 1.0MHz	C_{iss}		857	1030	
Output Capacitance		C_{oss}		97		pF
Reverse Transfer Capacitance	1 - 1.0IVII IZ	C_{rss}		71		
Switching ^c						
Turn-On Delay Time	V_{DD} = 15V, R_L = 1.8Ω, I_D = 1A, V_{GEN} = 10V, R_G = 6Ω	t _{d(on)}		3.3	5	
Turn-On Rise Time		t _r		4.7	7	nS
Turn-Off Delay Time		t _{d(off)}		26	39	113
Turn-Off Fall Time	17G - 022	t _f		4.1	6.2	

Notes:

- a. pulse test: PW ≤300µS, duty cycle ≤2%
- b. For DESIGN AID ONLY, not subject to production testing.
- b. Switching time is essentially independent of operating temperature.



Switching Test Circuit

Switchin Waveforms

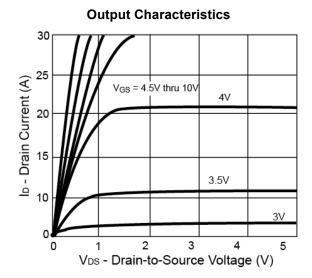
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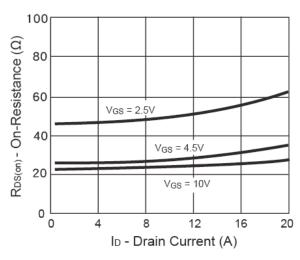
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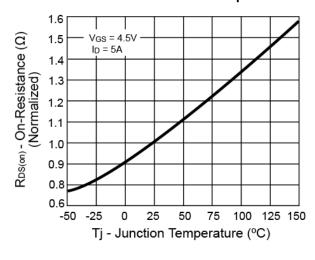
Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)



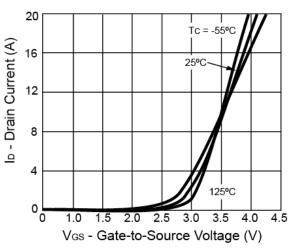
On-Resistance vs. Drain Current



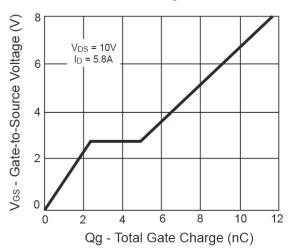
On-Resistance vs. Junction Temperature



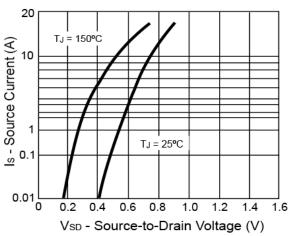
Transfer Characteristics



Gate Charge



Source-Drain Diode Forward Voltage



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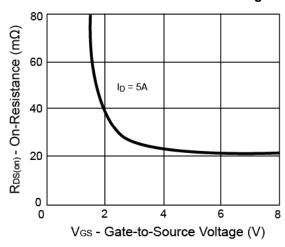


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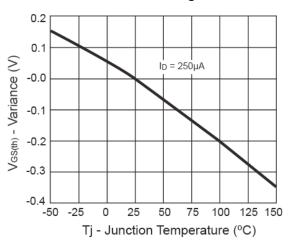


Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

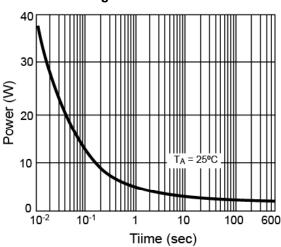
On-Resistance vs. Gate-Source Voltage



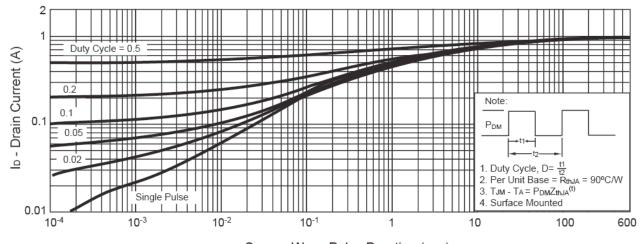
Threshold Voltage



Single Pulse Power



Normalized Thermal Transient Impedance, Junction-to-Ambient



Square Wave Pulse Duration (sec)

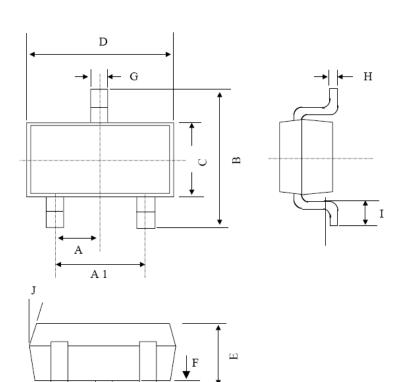
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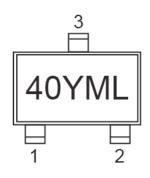


SOT-23 Mechanical Drawing



SOT-23 DIMENSION					
DIM	MILLIM	ETERS	INCHES		
DIIVI	MIN	MAX	MIN	MAX.	
Α	0.95	BSC	0.037	BSC	
A1	1.9	BSC	0.074	BSC	
В	2.60	3.00	0.102	0.118	
С	1.40	1.70	0.055	0.067	
D	2.80	3.10	0.110	0.122	
Е	1.00	1.30	0.039	0.051	
F	0.00	0.10	0.000	0.004	
G	0.35	0.50	0.014	0.020	
Н	0.10	0.20	0.004	0.008	
I	0.30	0.60	0.012	0.024	
J	5°	10°	5°	10°	

Marking Diagram



40 = Device Code

Y = Year Code

M = Month Code

(A=Jan, B=Feb, C=Mar, D=Apl, E=May, F=Jun, G=Jul, H=Aug,

I=Sep, J=Oct, K=Nov, L=Dec)

L = Lot Code

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TSM3400 30V N-Channel MOSFET

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